

HIGH CURRENT APPLICATION.

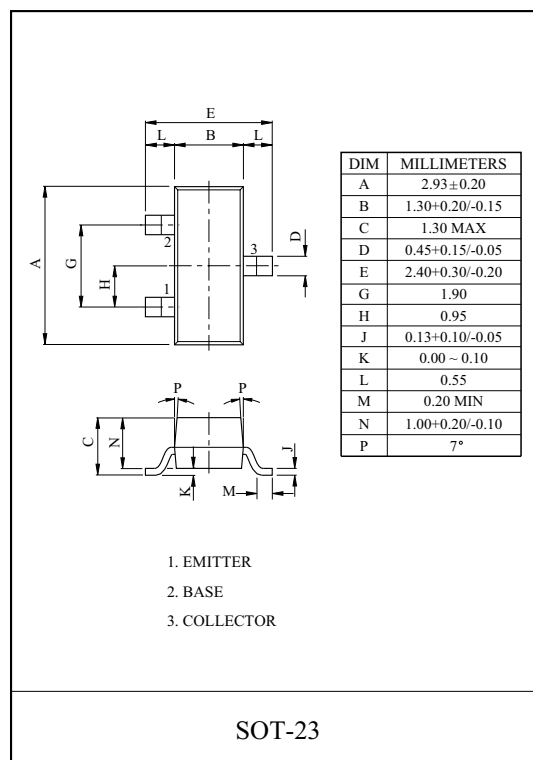
FEATURE

- Complementary to KTC8050S.

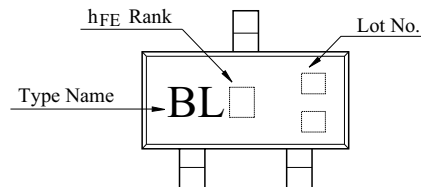
MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-35	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-800	mA
Emitter Current	I _E	800	mA
Collector Power Dissipation	P _C *	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

* P_C : Package Mounted On 99.5% Alumina (10×8×0.6mm)



Marking



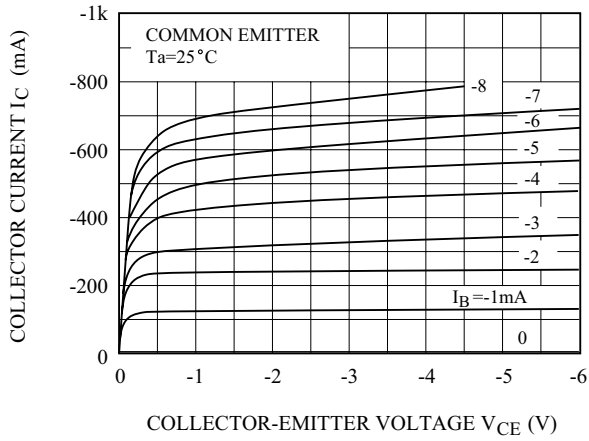
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =-15V, I _E =0	-	-	-50	nA
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =-0.5mA, I _E =0	-35	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-30	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =-1V, I _C =-50mA	100	-	300	
	h _{FE} (2)	V _{CE} =-1V, I _C =-350mA	60	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA	-	-	-0.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-1V, I _C =-500mA	-	-	-1.2	V
Transition Frequency	f _T	V _{CE} =-5V, I _C =-10mA	-	120	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz, I _E =0	-	19	-	pF

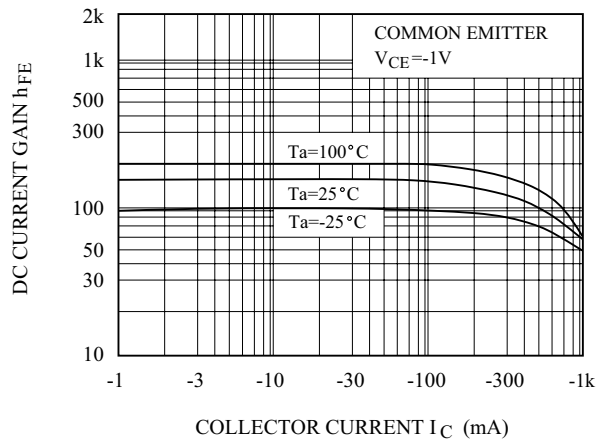
Note : h_{FE}(1) Classification C : 100 ~ 200, D : 150 ~ 300

KTC8550S

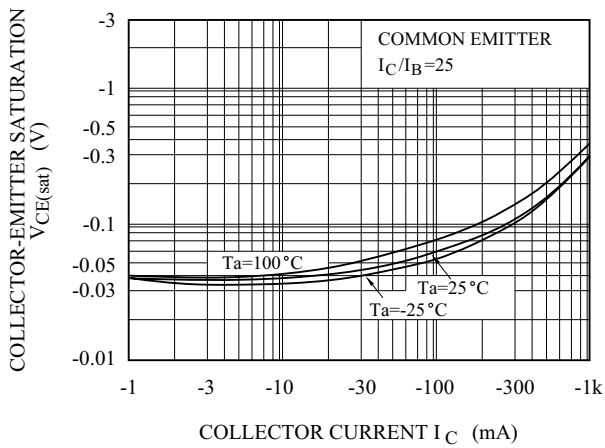
$I_C - V_{CE}$



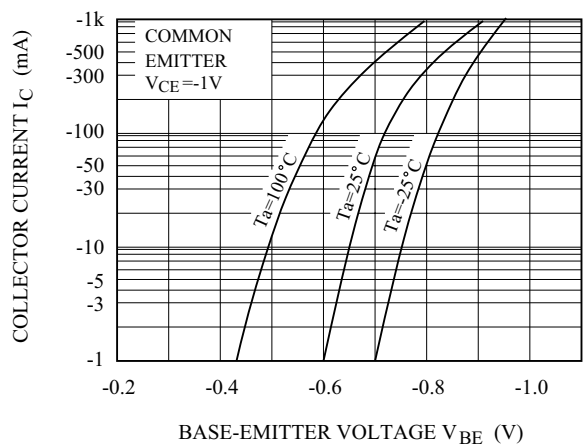
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_c - T_a$

